

isc N-Channel MOSFET Transistor

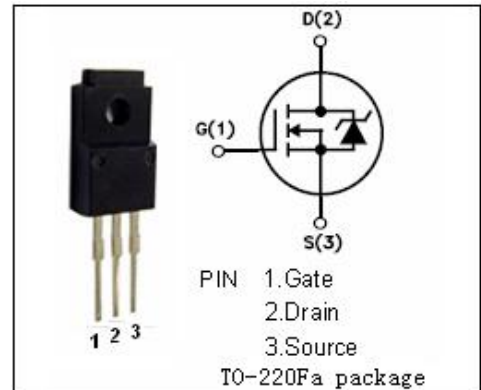
2SK757

DESCRIPTION

- Drain Current  $-I_D=10A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}= 200V(\text{Min})$

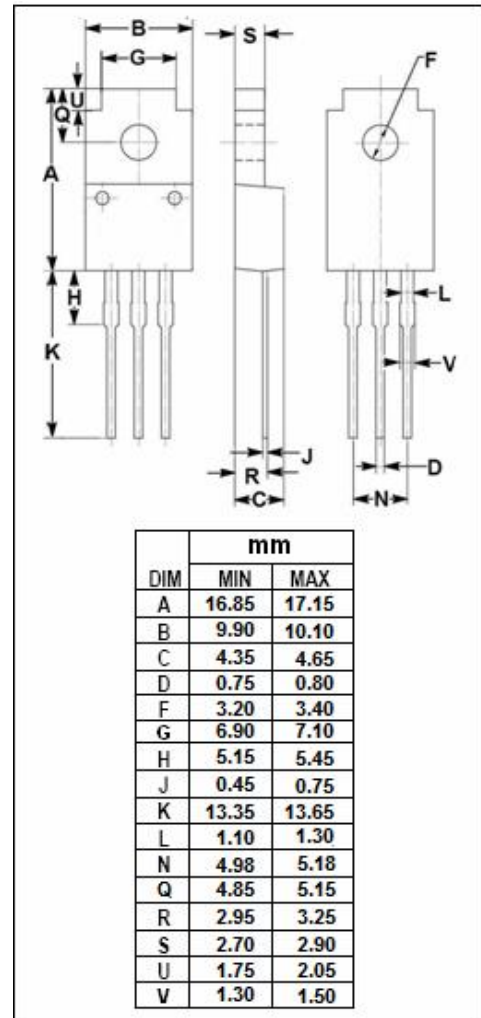
APPLICATIONS

- High speed power switching



ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	ARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	200	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $TC=25^\circ C$	10	A
$P_{tot}$	Total Dissipation@ $TC=25^\circ C$	50	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc N-Channel Mosfet Transistor****2SK757****• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> = 10mA	200			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =10 V <sub>GS</sub> ; I <sub>D</sub> =1mA	1.0		5.0	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 5A			0.33	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±16V; V <sub>DS</sub> = 0			±10	uA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =160V; V <sub>GS</sub> = 0			250	uA
V <sub>SD</sub>	Diode Forward Voltage	I <sub>F</sub> =10A; V <sub>GS</sub> =0		1.0		V